Abridged version

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High Quality Dielectric Film for $0.35\text{-}\mu m$ Design Rule Application by O3-TEOS-CVD Using Ethanol Pre-treatment

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Synopsis:

A new surface treatment involving the spin-coating of ethanol on a substrate prior to O3-tetraethylorthosilicate (TEOS) deposition by atmospheric pressure chemical vapor deposition (APCVD) was found to be very effective of improving the gap-filling properties and film quality. The deposited film has a flow-like surface shape, and can be used to fill trenches of $0.3\mu m$ width and $1.2\mu m$ depth, which could not be filled by conventional O3-TEOS APCVD. The effects of surface treating by some other organic solvents are also reported and a possible mechanism is presented.

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The body can be viewed from the next page.

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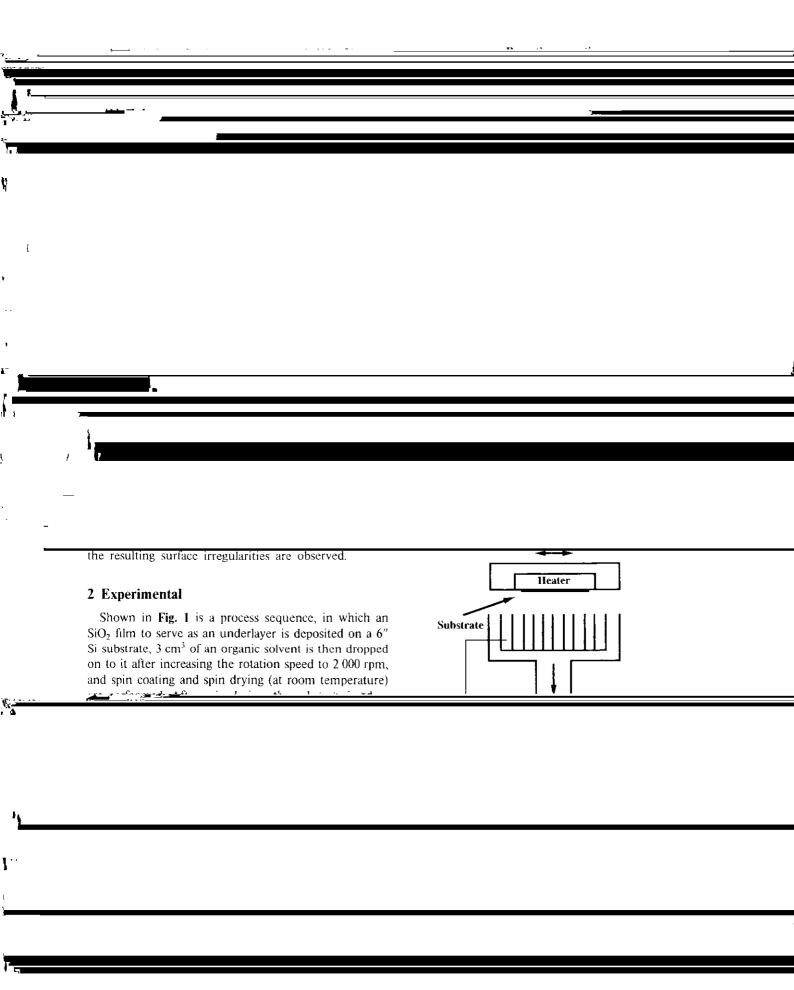






Synopsis:

A new surface treatment involving the spin-coating of ethanol on a substrate prior to O_3 -tetraethylorthosilicate (TEOS) deposition by atmospheric pressure chemical vapor



other than ethanol a plasma TEOS SiO_2 film deposited film, no appreciable improvement is apparent in the as an underlayer on the wiring nattern. Photo 2 (a) the gan-filling properties From these result it was

